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Sommario/riassunto

Field Effect Transistors is an essential read for anyone interested in the future of electronics, as it provides a comprehensive yet accessible exploration of innovative semiconductor devices and their applications, making it a perfect resource for both beginners and seasoned professionals in the field. Miniaturization has become the slogan of the electronics industry. Field Effect Transistors serves as a short encyclopedia for young minds looking for solutions in the miniaturization of semiconductor devices. It explores the characteristics, novel materials used, modifications in device structure, and advancements in model FET devices. Though many devices following Moore's Law have been proposed and designed, a complete history of the existing and proposed semiconductor devices is not available. This book focuses on developments and research in emerging semiconductor FET devices and their applications, providing unique coverage of topics covering recent advancements and novel concepts in the field of miniaturized semiconductor devices. Field Effect Transistors is an easy-to-understand guide, making it excellent for those who are new to the subject, giving insight and analysis of recent developments and developed semiconductor device structures along with their applications.